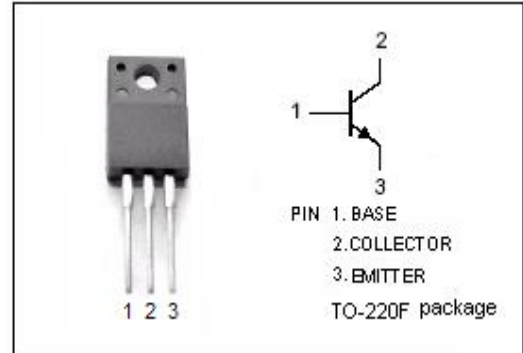


**isc Silicon NPN Power Transistor**
**2SD2137**
**DESCRIPTION**

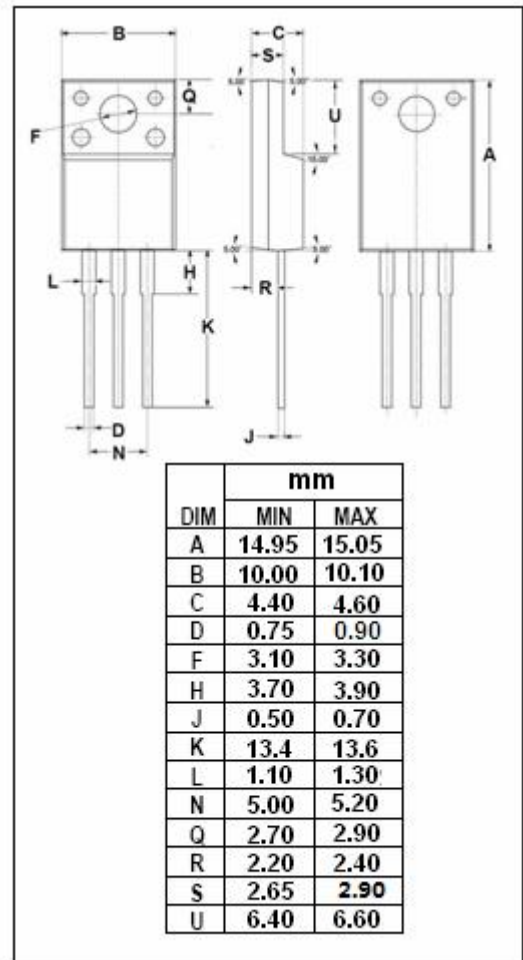
- Silicon NPN triple diffusion planar type
- Complementary to 2SB1417
- Low Collector to Emitter Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation
- Allowing supply with the radial taping


**APPLICATIONS**

- Designed for power amplifiers

**ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current-Continuous	3	A
I <sub>CM</sub>	Collector Current-Pulse	5	A
P <sub>T</sub>	Total Power Dissipation @T <sub>C</sub> =25°C	15	W
	Total Power Dissipation @T <sub>a</sub> =25°C	2	
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~150	°C



**isc Silicon NPN Power Transistor**
**2SD2137**
**ELECTRICAL CHARACTERISTICS**
**T<sub>j</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> =30mA, I <sub>B</sub> =0	60			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.375A			1.2	V
V <sub>BE(ON)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V			1.8	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 60V; I <sub>E</sub> = 0			100	μ A
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 30V; I <sub>B</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 6V; I <sub>C</sub> = 0			100	μ A
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 1A; V <sub>CE</sub> = 4V	70		250	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> =4V	10			
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 0.2A; V <sub>CE</sub> = 5V		30		MHz

**Switching times**

t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 1A I <sub>B1</sub> = -I <sub>B2</sub> = 0.1A, V <sub>CC</sub> ≈ 50V		0.3		μ s
t <sub>stg</sub>	Storage Time			2.5		μ s
t <sub>f</sub>	Fall Time			0.2		μ s

**◆ h<sub>FE-1</sub> Classifications**

Q	P
70-150	120-250

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